

ABSTRACT

The present invention relates to a method of manufacturing a semiconductor device, comprising the steps of: forming a sunken section in an insulating film formed on a substrate; forming a barrier metal film on said insulating film inclusive of said sunken section; forming a copper-based film over the entire surface so as to fill up said sunken section; and forming a copper-based metal interconnection, which comprises the step of polishing this substrate surface by the chemical mechanical polishing method, using a polishing slurry containing a silica polishing material, an oxidizing agent, an amino acid, a triazole-based compound and water, wherein a content ratio of said amino acid to said triazole-based compound (amino acid / triazole-based compound (weight ratio)) is 5 to 8.